

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of:

**Takashi OHSAWA**

SerialNo.: 10/621,357

Filed: July 18, 2003

For: SEMICONDUCTOR MEMORY  
DEVICE AND METHOD OF  
MANUFACTURING THE SAME

Atty. Docket No.: 002372.00044

Group Art Unit: 2818

Examiner: Andrew Q. Tran

**INFORMATION DISCLOSURE STATEMENT**

*Duplicate IDS at 08/30/05*  
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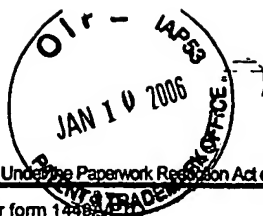
Sir:

Pursuant to his duty of good faith and candor as set forth in 37 C.F.R. § 1.56(a) Applicant submits herewith the references cited on the attached PTO/SB/08a. The references listed on the PTO/SB/08a form were cited in an European Search Report from a related application. A copy of the Search Report is also submitted herewith. Applicant respectfully requests that the Examiner consider these references in connection with the search of the prior art required by 37 C.F.R. § 1.104.

Applicant notes that each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed documents as a competent reference against the claims of the present application.

It is respectfully requested that the Examiner fully consider each item of information, initial the enclosed Form PTO/SB/08a in the appropriate place to indicate that the information has been considered, and return a copy of the initialed form to the undersigned in accordance with MPEP Section 609.

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PTO/SB/08a (08-03)

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet

1

of

1

**Complete if Known**

Application Number	10/621,357
Filing Date	July 18, 2003
First Named Inventor	Takashi OHSAWA
Art Unit	2818
Examiner Name	Andrew Q. Tran
Attorney Docket Number	002372.00044

**U.S. PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
at		US- 4,250,569	02/10/1981	Nobuo SASAKI, et al.	
at		US- 5,218,217	06/08/1993	Hidekazu ODA, et al.	
at		US- 5,712,501	01/27/1998	Robert B. DAVIES, et al.	
		US-			
		US-			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
at		JP 56-78156	06/26/1981		HOLL 27/10	
at		JP 56-119986	09/19/1981		GLIC 11/34	
at		JP 8-213624	08/20/1996		HOLL 29/786	

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
at		Patent Abstracts of Japan, Publication No. 56078156, Publication Date 06/26/1981, 1 page.	
at		Patent Abstracts of Japan, Publication No. 56119986, Publication Date 09/19/1981, 1 page.	
at		Patent Abstracts of Japan, Publication No. 08213624, Publication Date 08/20/1996, 1 page.	
at		Marx R. TACK, et al., "The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1980, pp. 1373-1382.	
at		Shigeki TOMISHIMA, et al., "A Long Data Retention SOI-DRAM with the Body Refresh Function", 1996 Symposium on VLSI Circuits Digest of Technical Papers, pp. 198-199.	

Examiner  
SignatureDate  
Considered

07/30/2006

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.  
Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.  
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